

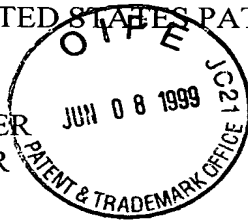
6/28/99

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

MARK I. GARDNER

MARK C. GILMER



Examiner: A. Mai

Serial No.: 09/079,759

Group Art Unit: 2814

Filed: May 15, 1998

Att'y Docket: 2000.002600/TT2587

For: METHOD OF MAKING AN  
ADVANCED ISOLATION  
STRUCTURE FOR HIGH DENSITY  
SEMICONDUCTOR DEVICES  
(as amended)

Amend

6/B

6-11-99

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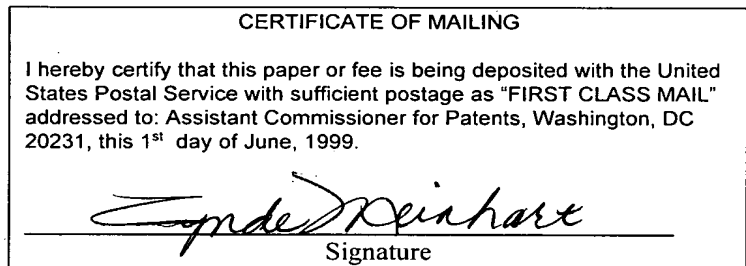
JUN 11 1999

TECHNOLOGY CENTER 2001

RESPONSE TO OFFICE ACTION DATED APRIL 6, 1999

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:



This paper is submitted in response to the Office Action dated April 6, 1999 for which the date for response is July 6, 1999.

IN THE CLAIMS

Please amend claims 20 and 28 as follows:

20. (amended) A method for forming an isolation trench in a semiconductor

substrate, said substrate having a surface, the method comprising:

forming a first recess in said substrate, said first recess having a first width of at  
most about 3000 Å and extending a first depth beneath the surface of said  
substrate;

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